

Abstract of the Disclosure:

The state of a ferroelectric transistor in a memory cell is read or stored, and the threshold voltage of further ferroelectric transistors in further memory cells in the memory matrix is increased during the reading or storing, or is increased permanently. A memory configuration including ferroelectric memory cells is also provided.

1000
900
800
700
600
500
400
300
200
100
0

MB/kc